

Features

- $V_{DS} = -20V, I_D = -0.8A$
- $R_{DS(ON)} < 590m\Omega @ V_{GS}=-4.5V$
- $R_{DS(ON)} < 900m\Omega @ V_{GS}=-2.5V$
- ESD Protection

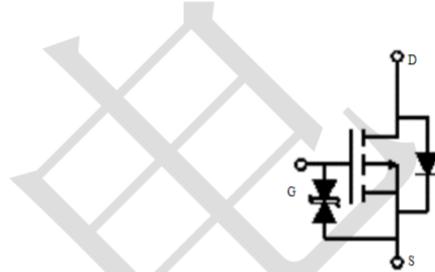
Application

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

Package and Pin Configuration



Circuit diagram



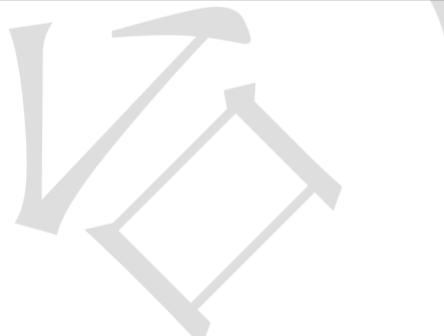
Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	-0.8	A
Pulsed Drain Current ($t=300\mu s$) ⁽¹⁾	I_{DM}	-1.4	A
Power Dissipation ⁽²⁾	P_D	280	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	452	$^\circ C/W$
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{STG}	-55~+150	$^\circ C$



Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$	-20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -20\text{V}, V_{GS} = 0\text{V}$			-1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 12\text{V}, V_{DS} = 0\text{V}$			± 10	μA
Gate threshold voltage ⁽³⁾	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-0.5	-0.75	-1.1	V
Drain-source on-resistance ⁽³⁾	$R_{\text{DS(on)}}$	$V_{GS} = -4.5\text{V}, I_{DS} = -550\text{mA}$			590	$\text{m}\Omega$
		$V_{GS} = -2.5\text{V}, I_{DS} = -450\text{mA}$			900	
Forward transconductance	g_{FS}	$V_{DS} = -5\text{V}, I_D = 500\text{mA}$		1		S
Dynamic characteristics⁽⁴⁾						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = -10\text{V}, \text{Freq.} = 1\text{MHz}$			60	pF
Output Capacitance	C_{oss}				6	
Reverse Transfer Capacitance	C_{rss}				5	
Switching Characteristics⁽⁴⁾						
Turn-on delay time	$t_{d(\text{on})}$	$V_{GS} = -4.5\text{V}, V_{DS} = -10\text{V}, I_D = -1\text{A}, R_{\text{GEN}} = 3\Omega$			0.45	us
Turn-on rise time	t_r				0.04	
Turn-off delay time	$t_{d(\text{off})}$				0.035	
Turn-off fall time	t_f				1.1	
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V_{DS}	$I_S = 0.15\text{A}, V_{GS} = 0\text{V}$			-1.2	V





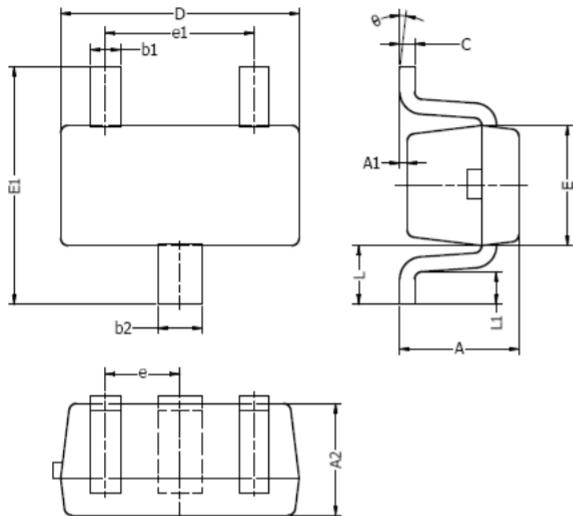
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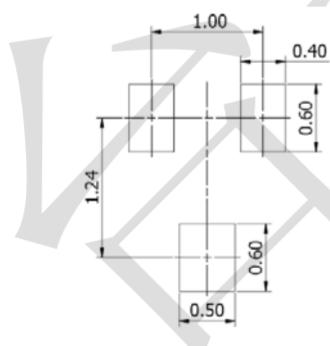
P-Channel Enhancement Mode MOSFET

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SOT523 Package Outline Drawing



Suggested Land Pattern



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	0.90	0.028	0.035
A1	0.00	0.10	0.000	0.004
A2	0.70	0.80	0.028	0.031
b1	0.15	0.25	0.006	0.010
b2	0.25	0.35	0.010	0.014
c	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
E1	1.45	1.75	0.057	0.069
e	0.50 TYP.		0.020 TYP.	
e1	0.90	1.10	0.035	0.043
L	0.40 REF.		0.016 REF.	
L1	0.10	0.30	0.004	0.012
θ	0°	8°	0°	8°

NOTES:

1. Above package outline conforms to JEITA EAJ ED-7500A SC-75A.
2. Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.